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N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
150	0.017 at V _{GS} = 10 V	75		
	$0.022 \text{ at V}_{GS} = 4.5 \text{ V}$	60		

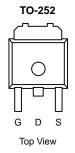
FEATURES

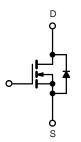
- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R_g Tested



APPLICATIONS

· Primary Side Switch





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C =	= 25 °C, unless othe	rwise noted)			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	150	- V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Dunis Comment /T 475 900b	T _C = 25 °C	I-	75		
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 125 °C	l _D	52.2		
Pulsed Drain Current		I _{DM}	175	А	
Continuous Source Current (Diode Conduction)		I _S	75		
Avalanche Current		I _{AR}	39		
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AR}	195	mJ	
Mayimum Dayor Dissination	T _C = 25 °C	P _D	189 ^b	W	
Maximum Power Dissipation	T _A = 25 °C] 'D [8.5 ^a	T VV	
Operating Junction and Storage Temperature Range	·	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
hungtion to Ambienta	t ≤ 10 s	R _{thJA}	15	20	°C/W
Junction-to-Ambient ^a	Steady State		42	53	
Junction-to-Case		R _{thJC}	0.5	0.9	

Notes

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static					l		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	150			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.2		3.0		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 150 V, V _{GS} = 0 V			1	50 μA	
		V _{DS} = 150 V, V _{GS} = 0 V, T _J = 125 °C			50		
		V _{DS} = 150 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	75			Α	
		V _{GS} = 10 V, I _D = 10 A		0.017			
5 1 2 2 2 2 1 5 1 b	D	V _{GS} = 10 V, I _D = 10 A, T _J = 125 °C		0.023		Ω	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A, T _J = 175 °C		0.028			
		V _{GS} = 4.5 V, I _D = 10 A		0.022			
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 10 A		52		S	
Dynamic ^a							
Input Capacitance	C _{iss}			2420		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		155			
Reverse Transfer Capacitance	C _{rss}			10			
Total Gate Charge ^c	Q_g			28	38		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$		5.5		nC	
Gate-Drain Charge ^c	Q_{gd}			5			
Gate Resistance	R_g		1		3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}			9	15		
Rise Time ^c	t _r	$V_{DD} = 75 \text{ V}, R_L = 5 \Omega$ $I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5$		10	15	ns	
Turn-Off Delay Time ^c	t _{d(off)}			25	45		
Fall Time ^c	t _f	Ω		10	24		
Source-Drain Diode Ratings and Char	racteristic (T	_C = 25 °C)					
Pulsed Current	I _{SM}				175	Α	
Diode Forward Voltage ^b	V_{SD}	I _F = 10 A, V _{GS} = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 10 A, dl/dt = 100 A/μs		85	99	ns	

Notes:

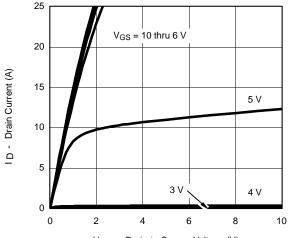
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

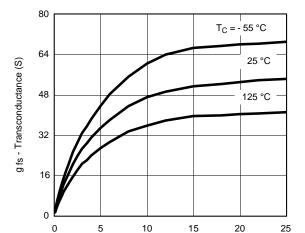




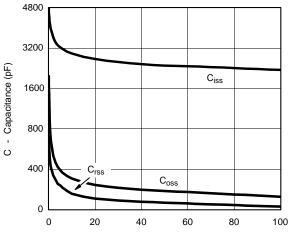
TYPICAL CHARACTERISTICS (25 °C unless noted)



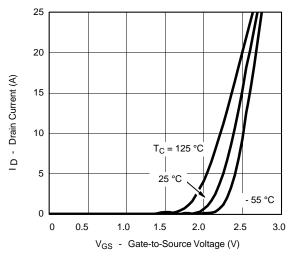
 $V_{DS}\,$ - Drain-to-Source Voltage (V) **Output Characteristics**



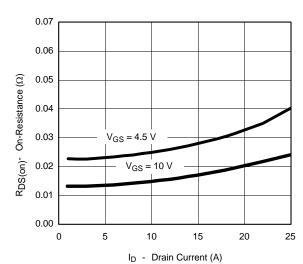
I_D - Drain Current (A) **Transconductance**



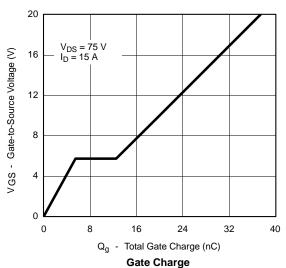
 $V_{DS}\,$ - Drain-to-Source Voltage (V) Capacitance



Transfer Characteristics



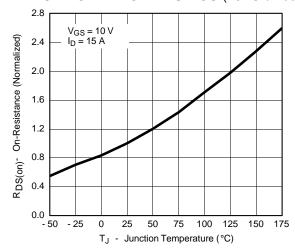
On-Resistance vs. Drain Current





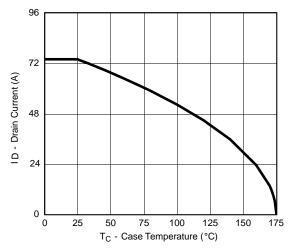
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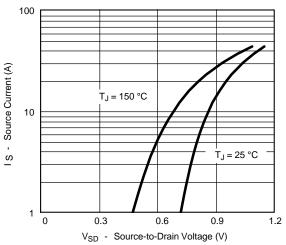


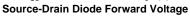
On-Resistance vs. Junction Temperature

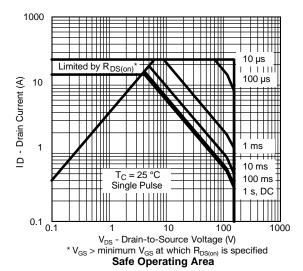
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature







Normalized Thermal Transient Impedance, Junction-to-Case

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